

OH COMPLIANCE



Pin Definition:

1. Source	8. Drair
2. Source	7. Drair
3. Source	6. Drair
4. Gate	5. Drair

source	6. Drain
Sate	5. Drain

Features

- Advance Trench Process Technology •
- High Density Cell Design for Ultra Low On-resistance •

Application

- DC-DC Converter •
- **Battery Power System**

Ordering Information

Part No.	Package	Packing				
TSM4459CS RLG SOP-8 2.5Kpcs / 13" Reel						
Note: "O" depote for Llelegen Free Dreduct						

Note: "G" denote for Halogen Free Product

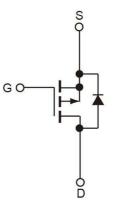
PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
	5.2 @ V _{GS} = -10V	4-
-30	9.5 @ V _{GS} = -4.5V	-17

30V P-Channel MOSFET

TSM4459

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current	$T_A = 25^{\circ}C$	- I _D -	-17	А	
	$T_{A} = 25^{\circ}C$ $T_{A} = 70^{\circ}C$		-13.6		
Pulsed Drain Current		I _{DM}	-68	А	
Maximum Power Dissipation Note a.	$T_A = 25^{\circ}C$	P	2.5	w	
Maximum Power Dissipation	$T_A = 70^{\circ}C$	P _D	1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temp	erature Range	T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Ambient Thermal Resistance Note a.	RƏ _{JA}	50	°C/W

Notes:

a. The Device Surface Mounted on 1inch² FR4 Board with 2oz copper.



TSM4459 30V P-Channel MOSFET

Electrical Specifications ($T_A = 25^{\circ}C$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-1		-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
Ducia Course On Otata Dacistance	$V_{GS} = -10V, I_{D} = -9A$			4	5.2	mΩ
Drain-Source On-State Resistance ^a	$V_{GS} = -4.5V, I_{D} = -9A$	R _{DS(ON)}		7	9.5	
Diode Forward Voltage	I _S = -18A, V _{GS} = 0V	V _{SD}		0.8		V
Dynamic						
Total Gate Charge		Qg		78.4		
Gate-Source Charge	$V_{DS} = -24V, I_D = -17A,$	Q _{gs}		25.1		nC
Gate-Drain Charge	$V_{GS} = -4.5V$	Q _{gd}		38.7		
Gate Resistance	f = 1.0MHz	R _g		2.88		Ω
Input Capacitance		C _{iss}		6205		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	C _{oss}		963		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		330		
Switching						
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega,$ $V_{GEN} = -10V,$	t _{d(on)}		75.2		
Turn-On Rise Time		t _r		33.8		
Turn-Off Delay Time		t _{d(off)}		275		nS
Turn-Off Fall Time	$R_G = 4.7\Omega$	t _f		92.1		

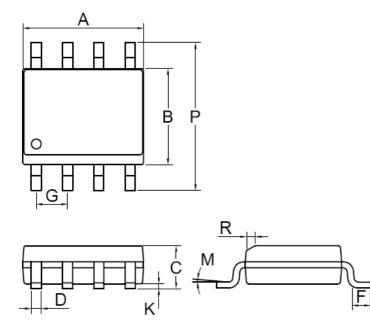
Notes:

a. pulse test: PW \leq 300µS, duty cycle \leq 2%



TSM4459 30V P-Channel MOSFET

SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM MILLIM		ETERS	INCHES		
DIN	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05BSC		
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



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